

2-20-07

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Appn. Number: 10/609.157

Appn. Filed: Jun/27/2003

Applicant: Hai Jiang

Title: Programmable Metallization Cell Memory with
Multiple Extra-Small Resistive Elements

Examiner: Pho M. Luu/2824

Please do not
enter
3/20/07
VTN

Feb. 15, 2007

Pleasanton, CA

Commissioner for Patents

P.O. Box 1450

Alexandria, Virginia 22313-1450

Sir,

Below are the response to the Office Action mailed on Nov. 28, 2006 and new claim status:

Claim rejections-35USC 102

Claim 32-34 are rejected under 35 U.S.C. 102(e) as being anticipated by Gilton. (US.2003/0194865).

Regarding claims 32-34, Gilton in Figure 3 disclosed a memory device (memory cell 120) comprising:

A resistive layer with a plurality of solid electrolyte element (110) and a metallic layer(112) and wherein the resistive layer is a layer with plurality of solid electrolyte element(110)embedded in an insulator layer(200) and wherein the